AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

Claims 1-3. (Canceled)

4. (Currently Amended) ~~The method of claim 3, wherein:~~ A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species for direct oxidation of the substrate to form a chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed,

the substrate being immersed in the oxidizing solution of different concentrations, and

the concentration of the oxidizing solution being altered from a low-concentration oxidizing solution to a high-concentration oxidizing solution, and

the low-concentration oxidizing solution has a lower concentration than an azeotropic concentration; and

the high-concentration oxidizing solution has a concentration more than or equal to the azeotropic concentration.

5. (Currently Amended) ~~The method of claim 3, wherein~~ A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species for direct oxidation of the substrate to form a chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed,

the substrate being immersed in the oxidizing solution of different concentrations, and

the concentration of the oxidizing solution being altered from a low-concentration oxidizing solution to a high-concentration oxidizing solution, and

in the oxide film forming step, the low-concentration oxidizing solution is concentrated to prepare the high-concentration oxidizing solution.

6. (Currently Amended) The method of claim [[1]]7, wherein

in the oxide film forming step, the chemical oxide film is grown on the substrate surface by applying voltage to the substrate on which the chemical oxide film is to be formed.

7. (Currently Amended) ~~The method of claim 1, wherein~~ A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species for direct oxidation of the substrate to form a chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed,

the substrate on which the chemical oxide film is to be formed contains, on the surface, at least one component selected from the group consisting of monocrystal silicon, polycrystalline silicon, amorphous silicon, continuous grain silicon, silicon carbide, and silicon germanium.

Claim 8. (Canceled)

9. (Currently Amended) ~~The method of claim 8, wherein~~ A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species for direct oxidation of the substrate to form a chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed,

wherein

the oxidizing solution is an azeotropic mixture containing: at least one solution selected from the group consisting of nitric acid, perchloric acid, sulfuric acid, ozone-dissolving water, aqueous hydrogen peroxide, a mixed solution of hydrochloric acid and aqueous hydrogen peroxide, a mixed solution of sulfuric acid and aqueous hydrogen peroxide, a mixed solution of aqueous ammonia and aqueous hydrogen peroxide, a mixed solution of sulfuric acid and nitric acid, aqua regia, and boiling water; a gas thereof; or a mixed solution thereof

~~the oxidizing solution is an azeotropic mixture~~.

10. (Original) The method of claim 9, wherein

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the oxidizing solution contains at least one solution selected from the group consisting of azeotropic nitric acid which is an azeotropic mixture with water, azeotropic sulfuric acid which is an azeotropic mixture with water, and azeotropic perchloric acid which is an azeotropic mixture with water.

11. (Currently Amended) The method of claim [[1]]4, wherein

the oxide film forming step is carried out at 200°C or lower temperatures.

12. (Currently Amended) The method of claim [[1]]4, further comprising, after forming the chemical oxide film, [[the]]a step of forming an insulating film on the chemical oxide film.

13. (Currently Amended) ~~The method of claim 1, wherein the oxide film forming step comprises the steps of:~~ A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species below azeotropic concentration for direct oxidation of the substrate to form a first chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed; and

concentrating the oxidizing solution below azeotropic concentration up to or in excess of an azeotropic concentration with the substrate being immersed in that oxidizing solution to form a second oxide film on the first oxide film.

14. (Original) The method of claim 7, wherein

the substrate on which the chemical oxide film is to be formed contains silicon carbide on the surface.

15. (Currently Amended) The method of claim [[8]]9, wherein

the oxidizing solution is nitric acid.

16. (Currently Amended) The method of claim [[1]]4, further comprising, after the oxide film forming step, the step of subjecting the chemical oxide film(s) to nitriding.

17. (Currently Amended) A thin film transistor manufactured by the method of claim [[1]]7, comprising the chemical oxide film formed by oxidation in an oxidizing solution.

18. (Original) A thin film transistor of claim 17, wherein the chemical oxide film has a relatively high atomic density near the substrate.

Claim 19. (Canceled)

20. (Previously Presented) A display containing the thin film transistor of claim 17.

21. (Currently Amended) A method of modifying an oxide film, comprising the step of

performing the oxide film forming step of claim [[1]]7 on an oxide film having a non-uniform thickness to improve quality of the oxide film.

22. (Currently Amended) A method of modifying an oxide film, comprising the step of

performing the oxide film forming step of claim [[1]]7 on an oxide film having non-uniform quality to improve the quality of the oxide film.

23. (Withdrawn) A method of forming an oxide film, comprising the steps of:

bringing a semiconductor in contact with an oxidizing solution below azeotropic concentration or a gas thereof to form a first chemical oxide film on a surface of the semiconductor; and

bringing the semiconductor on which the first chemical oxide film is formed in contact with an oxidizing solution of or in excess of azeotropic concentration or a gas thereof to form a second chemical oxide film.

24. (Withdrawn) A method of forming an oxide film, comprising the steps of:

reacting an oxidizing solution of a low concentration or a gas thereof with a surface of a semiconductor to form a first chemical oxide film on the surface of the semiconductor; and

reacting an oxidizing solution of a high concentration or a gas thereof to form a second chemical oxide film on the first chemical oxide film.

25. (Withdrawn) The method of claim 23, wherein

the step of forming the second chemical oxide film is carried out while the oxidizing solution used to form the first chemical oxide film is being concentrated.

26. (Withdrawn) The method of claim 23, wherein

the second chemical oxide film is formed so that the second chemical oxide film is thicker than the first chemical oxide film.

27. (Withdrawn) The method of claim 23, wherein

the step of forming the first chemical oxide film and the step of forming the second chemical oxide film are carried out with the semiconductor being immersed in the oxidizing solution.

28. (Withdrawn) The method of claim 23, wherein

the semiconductor contains at least one component selected from the group consisting of monocrystal silicon, polycrystalline silicon, amorphous silicon, silicon carbide, and silicon germanium.

29. (Withdrawn) The method of claim 24, wherein

the oxidizing solution of a high concentration or a gas thereof is an oxidizing solution of or in excess of azeotropic concentration or a gas thereof.

30. (Withdrawn) The method of claim 23, wherein

the oxidizing solution or the gas thereof contains: at least one solution selected from the group consisting of nitric acid, perchloric acid, sulfuric acid, ozone-dissolving water, aqueous hydrogen peroxide, a mixed solution of hydrochloric acid and aqueous hydrogen peroxide, a mixed solution of sulfuric acid and aqueous hydrogen peroxide, a mixed solution of aqueous ammonia and aqueous hydrogen peroxide, a mixed solution of sulfuric acid and nitric acid, aqua regia, and boiling water; a gas thereof; or a mixture thereof.

31. (Withdrawn) The method of claim 24, wherein:

the oxidizing solution of a low concentration or the gas thereof contains: at least one solution below azeotropic concentration selected from the group consisting of an

aqueous solution of nitric acid, an aqueous solution of sulfuric acid, and an aqueous solution of perchloric acid; or a gas thereof; and

the oxidizing solution of a high concentration or the gas thereof contains: at least one solution of or in excess of azeotropic concentration selected from the group; or a gas thereof.

32. (Withdrawn) The method of claim 23, further comprising, after forming the chemical oxide films on the surface of the semiconductor, the step of subjecting the chemical oxide films to nitriding.

33. (Withdrawn) A method of manufacturing a semiconductor device, comprising the oxide film forming step of

forming a chemical oxide film by the method of claim 23.

34. (Withdrawn) A method of manufacturing a semiconductor device, comprising the steps of:

reacting an oxidizing solution of a low concentration or a gas thereof with a surface of a semiconductor to form a first chemical oxide film on the surface of the semiconductor; and

reacting an oxidizing solution of a high concentration or a gas thereof to form a second chemical oxide film on the first chemical oxide film.